

(2) 研究業績リスト

・ 査読付学術論文

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1. T. Akasaka, Y. Araki, M. Nakata, and I. Shimizu*, "In Situ Ellipsometric Observations of the Growth of Silicon Thin Films from Fluorinated Precursors, SiF_nH_m ($n+m \leq 3$)", Jpn. J. Appl. Phys. **32**, (1993) pp. 2607-2612. (IF=1.122), (Times Cited: 7)
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